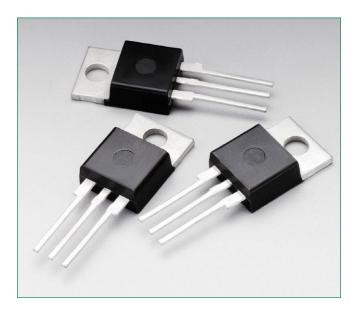


MAC15 Series





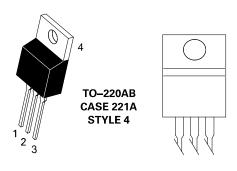
Description

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- These Devices are Pb–Free and are RoHS Compliant

Pin Out



Functional Diagram



Additional Information







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Maximum Ratings ($T_J = 25$ °C unless otherwise noted)						
Rating		Symbol	Value	Unit		
	MAC15A6G MAC15-8G, MAC15A8G AC15-10G, MAC15A10G	V _{DRM} , V _{RRM}	400 600 800	V		
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, $T_c = 90^{\circ}$	C)	I _{T (RMS)}	15	А		
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 F Preceded and Followed by Rated Current	Hz, T _J = 125°C)	I _{TSM}	150	А		
Peak Gate Voltage (Pulse Width ::: 1.0 μsec; TC = 90°C)		$V_{\scriptscriptstyle GM}$	10	V		
Circuit Fusing Consideration (t = 8.3 ms)		l²t	93	A²sec		
Peak Gate Power ($T_c = +80^{\circ}\text{C}$, Pulse Width = 1.0 µs)		P_{GM}	20	W		
Peak Gate Current (Pulse Width ::: 1.0 μsec; TC = 90°C)		I _{GM}	2.0	А		
Average Gate Power (t = 8.3 ms, $T_c = 80$ °C)		P _{G (AV)}	0.5	W		
Operating Junction Temperature Range		T _J	-40 to +125	°C		
Storage Temperature Range		T _{stg}	-40 to +150	°C		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{ejc} R _{eja}	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Pur 10 seconds	poses, 1/8" from case for	T _L	260	°C

Electrical Characteristics - OFF (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	1.0	A
$(V_D = V_{DRM} = V_{RRM}, Gate Open)$	T = 125°C	I _{BRM}	-	-	2.0	mA

Electrical Characteristics - ON (T, = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) (I _{TM} = ±21 A Peak)		V _{TM}	_	1.3	1.6	V
	MT2(+), G(+)		_	_	50	
Gate Trigger Current (Continuous dc)	MT2(+), G(-)		_	_	50	mA
(Continuous ac) $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)	GT	_	_	50	MA
()	MT2(-), G(+)				75	
	MT2(+), G(+)		0.5	0.62	1.3	
Gate Trigger Voltage (Continuous dc)	MT2(+), G(-)	.,	0.5	0.57	1.3	V
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)	V _{GT}	0.5	0.65	1.3	V
()	MT2(-), G(+)		0.5	0.74	1.3	
	MT2(+), G(+)		0.2	-	_	
Gate Non–Trigger Voltage	MT2(+), G(-)	/	0.2	-	_	V
$(T_J = 125^{\circ}C)$ $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)	V _{GD}	0.2	-	_	V
	MT2(-), G(+)		0.2	-	_	
Holding Current ($V_D = 12 V_{dc'}$ Gate Open, Initiating Current = ± 20	00 mA))	I _H	_	6.0	40	mA

^{2.} Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

^{1.} V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

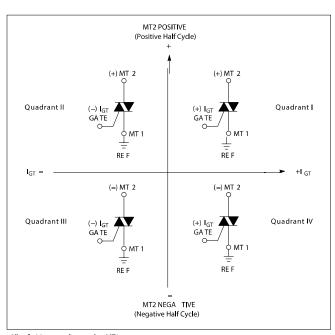


Dynamic Characteristics						
Characteristic	Symbol	Min	Тур	Max	Unit	
Critical Rate of Rise of Commutation Voltage (V_D = Rated $V_{DRM'}$ I_{TM} = 21 A, Commutating di/dt = 7.6 A/ms, Gate Unenergized, TC = 80°C)	dV/dt	-	5.0	_	V/µs	

Voltage Current Characteristic of SCR

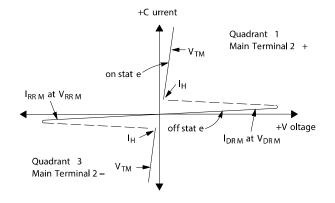
Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
l _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in—phase signals (using standard AC lines) quadrants I and III are used







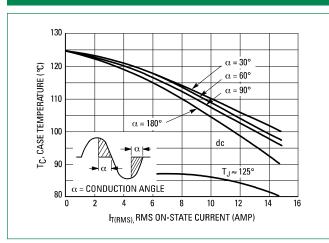


Figure 2. On-State Power Dissipation

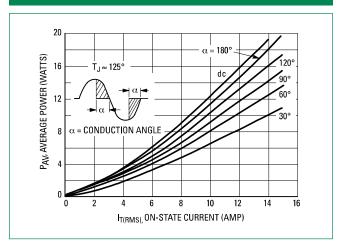


Figure 3. Typical Gate Trigger Voltage

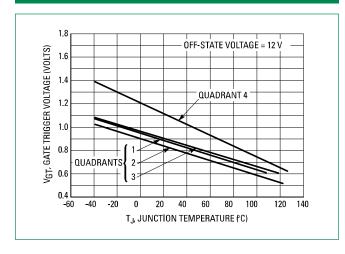


Figure 4. Typical Gate Trigger Current

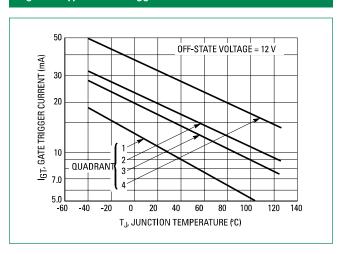




Figure 5. On-State Characteristics

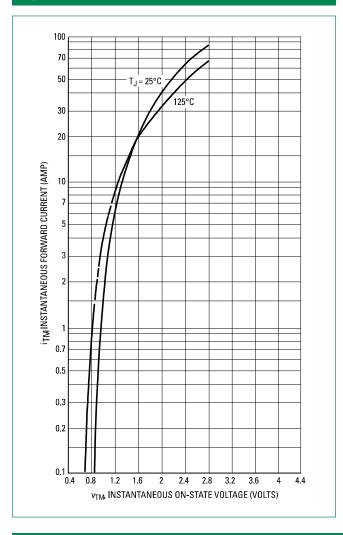


Figure 6. Typical Holding Current

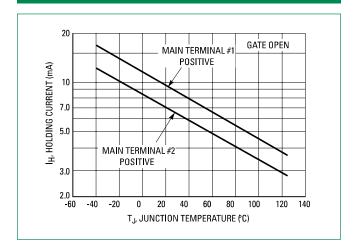


Figure 7. Maximum Non-Repetitive Surge Current

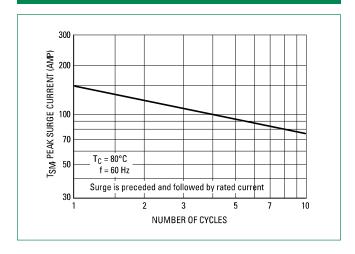
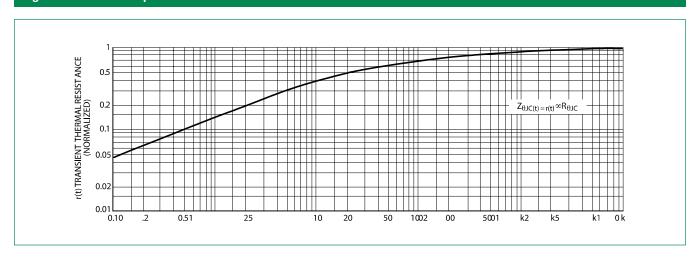
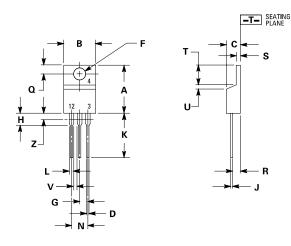


Figure 8. Thermal Response

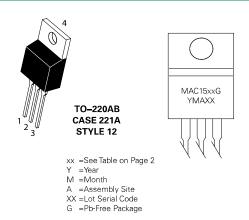




Dimensions



Part Marking System



D:	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
К	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
s	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

Ordering	Information
Oldoning	IIIIOIIIIacioii

Device	Device Marking	Package	Shipping
MAC15-8G	MAC15-8		
MAC15-10G	MAC1510		
MAC15A6G	MAC15A6	TO-220AB (Pb-Free)	500 Units/Box
MAC15A8G	MAC15A8	(, 5, , , , ,	
MAC15A10G	MAC15A10		

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.